



Micro Commercial Components
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2SD557

NPN Silicon Power Transistors

Features

- With TO-3 package
- High power audio amplifier applications

Maximum Ratings

Symbol	Rating	Rating	Unit
V_{CEO}	Collector-Emitter Voltage	140	V
V_{CBO}	Collector-Base Voltage	140	V
V_{EBO}	Emitter-Base Voltage	7.0	V
I_{CP}	Peak Collector Current	20	A
I_C	Collector Current	15	A
P_C	Collector power dissipation	120	W
T_J	Junction Temperature	-55 to +150	°C
T_{STG}	Storage Temperature	-55 to +150	°C

Electrical Characteristics @ 25°C Unless Otherwise Specified

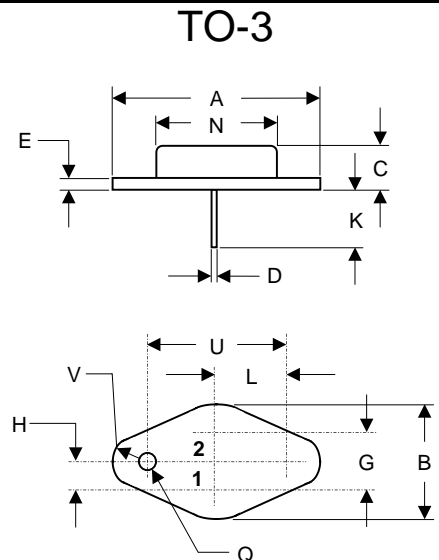
Symbol	Parameter	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ($I_C=200\text{mA}$, $I_B=0$)	140	---	Vdc
I_{CBO}	Collector-Base Cutoff Current ($V_{CB}=140\text{Vdc}$, $I_E=0$)	---	2.0	mAdc
I_{EBO}	Emitter-Base Cutoff Current ($V_{EB}=7.0\text{Vdc}$, $I_C=0$)	---	5.0	mAdc

ON CHARACTERISTICS

h_{FE}	Forward Current Transfer ratio ($I_C=5.0\text{Adc}$, $V_{CE}=4.0\text{Vdc}$)	30	---	---
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage ($I_C=10\text{Adc}$, $I_B=1.0\text{Adc}$)	---	1.0	Vdc
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage ($I_C=16\text{Adc}$, $I_B=4.0\text{Adc}$)	---	2.0	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage ($I_C=8.0\text{Adc}$, $V_{CE}=2.0\text{Vdc}$)	---	1.5	Vdc



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	1.550	REF	39.37	REF	
B	----	1.050	----	26.67	
C	.250	.335	6.35	8.51	
D	.038	.043	0.97	1.09	
E	0.55	0.70	1.40	1.77	
G	.430	BSC	10.92	BSC	
H	.215	BSC	5.46	BSC	
K	.440	.480	11.18	12.19	
L	.665	BSC	16.89	BSC	
N	----	.830	----	21.08	
Q	.151	.165	3.84	4.19	∅
U	1.187	BSC	30.15	BSC	
V	.131	.188	3.33	4.77	